



UTG75N120LLS1

Preliminary

Insulated Gate Bipolar Transistor

1200V TRENCH GATE FIELD-STOP IGBT

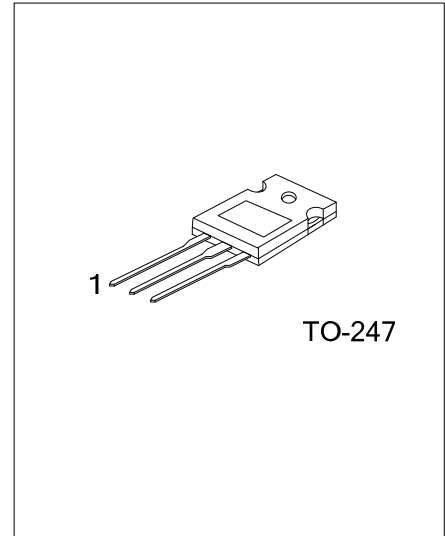
DESCRIPTION

The UTC **UTG75N120LLS1** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

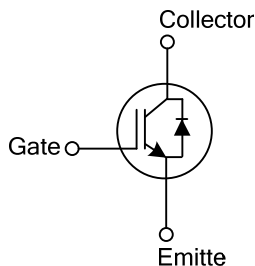
The UTC **UTG75N120LLS1** is suitable for the resonant or soft switching applications.

FEATURES

- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: $V_{CE(sat)}$, typ = 1.84V @ $I_C=75A$, $V_{GE}=15V$ ($T_C=25^\circ C$)



SYMBOL



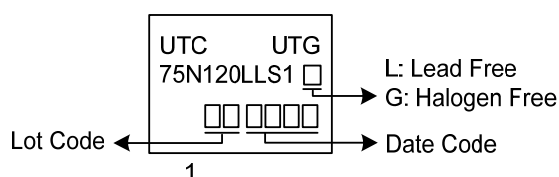
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTG75N120LLS1L-T47-T	UTG75N120LLS1G-T47-T	TO-247	G	C	E	Tube

Note: Pin Assignment: G: Gate C: Collector E: Emitter

UTG75N120LLS1G-T47-T	(1)Packing Type	(1) T: Tube
	(2)Package Type	(2) T47: TO-247
	(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V _{CES}	1200	V
Gate-Emitter Voltage		V _{GES}	±20	V
Continuous Collector Current	T _C =25°C	I _C	150	A
	T _C =100°C		75	A
Collector Current Pulsed (Note 1)		I _{CM}	300	A
Diode Forward Current	T _C =25°C	I _F	150	A
	T _C =100°C		75	A
Short Circuit Withstand Time V _{GE} = 15V, V _{CC} ≤ 200V Allowed number of short circuits < 1000 Time between short circuits: ≥1.0s T _{VJ} = 25°C		t _{sc}	8	μs
Power Dissipation (T _C =25°C)		P _D	285	W
Operating Junction Temperature		T _J	-40 ~ +150	°C
Storage Temperature Range		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Absolute maximum ratings are those values beyond which the device could be permanently damaged.

2. Pulse width limited by maximum junction temperature.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	θ _{JC}	0.44	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off Characteristics						
Collector-Emitter Breakdown Voltage	BV _{CES}		1200			V
Collector Cut-Off Current	I _{CES}	V _{CE} =V _{CES} , V _{GE} =0V			5	μA
G-E Leakage Current	I _{GES}	V _{GE} =V _{GES} , V _{CE} = 0V			±100	nA
On Characteristics						
Gate to Emitter Threshold Voltage	V _{GE(TH)}	I _C =250μA, V _{CE} =V _{GE}	4.5		7.5	V
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =75A, V _{GE} =15V		1.84	2.3	V
		I _C =75A, V _{GE} =15V, T _C =125°C		2.4		V
Dynamic Characteristics						
Input Capacitance	C _{IES}	V _{CE} =25V, V _{GE} =0V, f=1MHz		6560		pF
Output Capacitance	C _{OES}			152		pF
Reverse Transfer Capacitance	C _{RES}			61.6		pF
Switching Characteristics						
Total Gate Charge	Q _G	V _{CE} =600V, I _C =75A, V _{GE} =15V		27.3		nC
Gate-Emitter Charge	Q _{GE}			52.6		nC
Gate-Collector Charge	Q _{GC}			14.5		nC
Turn-On Delay Time	t _{DON}	V _{CC} =600V, I _C =75A, R _G =5Ω, V _{GE} =0~15V, L=500uH		39.5		ns
Rise Time	t _R			77.3		ns
Turn-Off Delay Time	t _{DOFF}			248		ns
Fall Time	t _F			235		ns
Turn-On Switching Loss	E _{ON}			5.95		mJ
Turn-Off Switching Loss	E _{OFF}			5.87		mJ
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Forward Voltage Drop	V _{FM}	I _F =75A		2.52		V
Reverse Recovery Time	t _{rr}	I _F =75A, dI/dt=100A/μS		75.5		ns
Reverse Recovery Charge	Q _{rr}			1.54		μC

■ TEST CIRCUIT AND WAVEFORMS

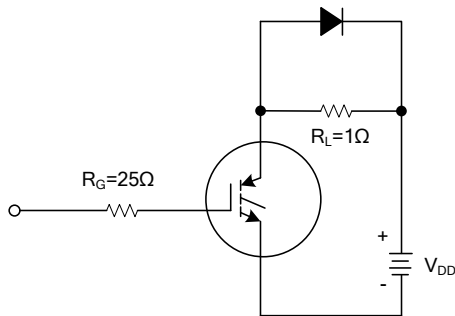


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

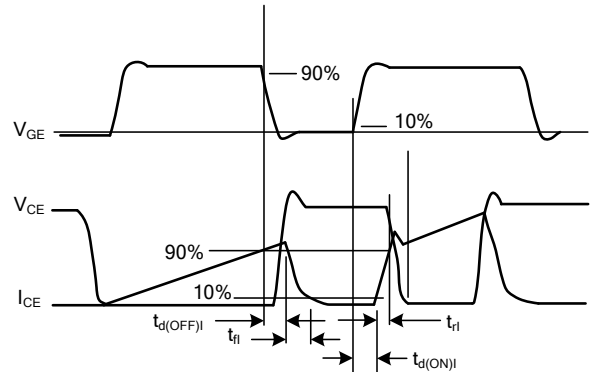


Fig 2. SWITCHING TEST WAVEFORMS

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